

**NOR GATE**

- 4000B-DUAL 3 INPUT PLUS INVERTER**
- 4001B-QUAD 2 INPUT**
- 4002B-DUAL 4 INPUT**
- 4025B TRIPLE 3 INPUT**

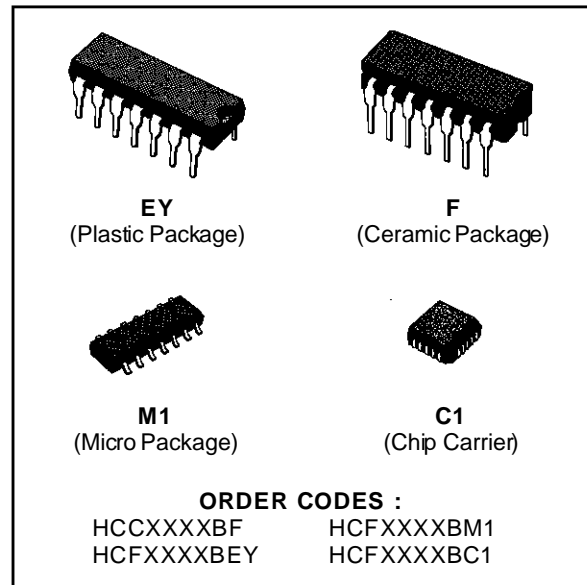
- PROPAGATION DELAY TIME = 60 ns (typ.) AT  $C_L = 50$  pF,  $V_{DD} = 10$  V
- BUFFERED INPUTS AND OUTPUTS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20 V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25 °C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

**DESCRIPTION**

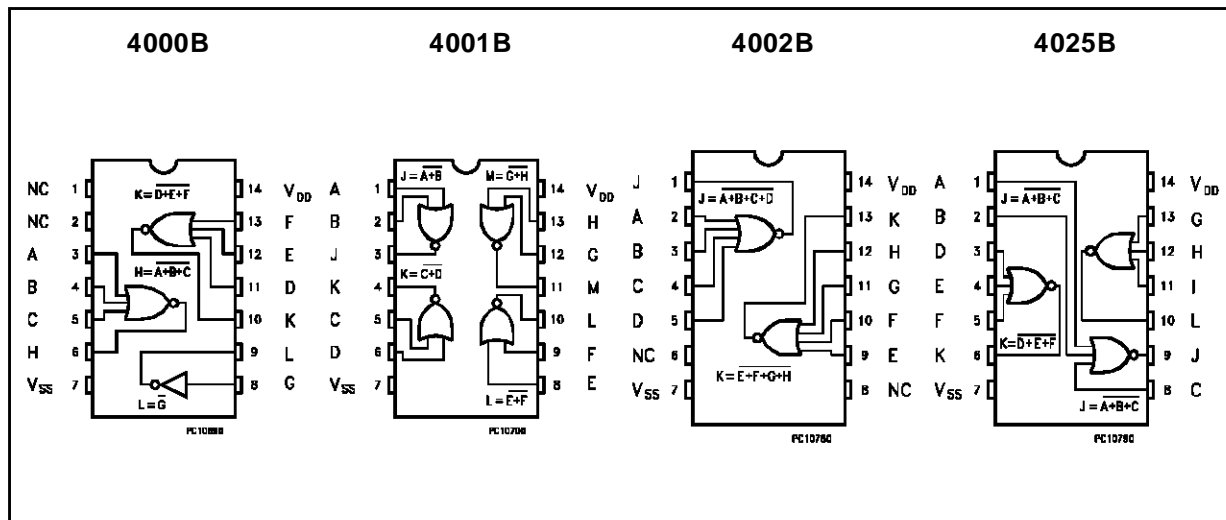
The **HCC4000B**, **HCC4001B**, **HCC4002B** and **HCC4025B** (extended temperature range) and **HCF4000B**, **HCF4001B**, **HCF4002B** and **HCF4025B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in line plastic or ceramic package and plastic

micropackage.

The **HCC/HCF4000B**, **HCC/HCF4001B**, **HCC/HCF4002B** and **HCC/HCF4025B** nor gate provide the system designer with direct implementation of the nor function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.



**PIN CONNECTIONS**



## HCC/HCF4000B-4001B-4002B-4025B

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### ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage: <b>HCC</b> Types <b>HCF</b> Types	-0.5 to +20	V
		-0.5 to +18	V
V <sub>i</sub>	Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200	mW
		100	mW
T <sub>op</sub>	Operating Temperature: <b>HCC</b> Types <b>HCF</b> Types	-55 to +125	°C
		-40 to +85	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

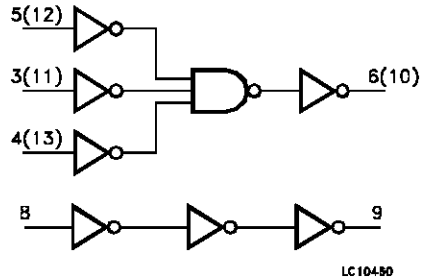
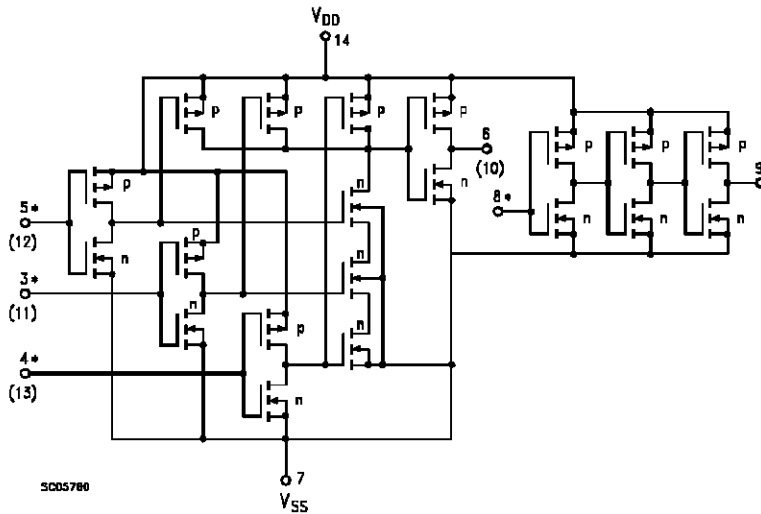
\* All voltage values are referred to V<sub>SS</sub> pin voltage.

### RECOMMENDED OPERATING CONDITIONS

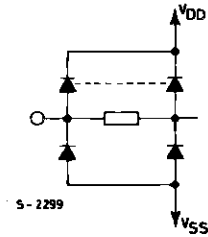
Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage: <b>HCC</b> Types <b>HCF</b> Types	3 to 18	V
		3 to 15	V
V <sub>i</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature: <b>HCC</b> Types <b>HCF</b> Types	-55 to +125	°C
		-40 to +85	°C

SCHEMATIC AND LOGIC DIAGRAMS

4000B

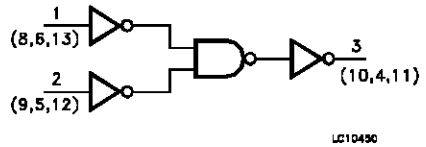
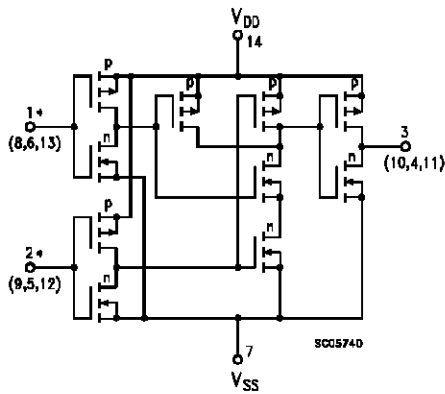


INVERTER AND 1 OF 2 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR SECOND GATE)

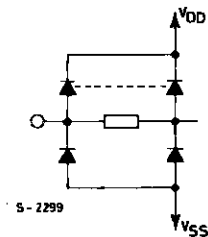


ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

4001B



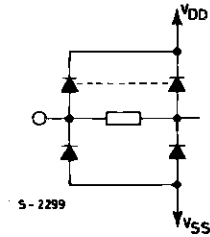
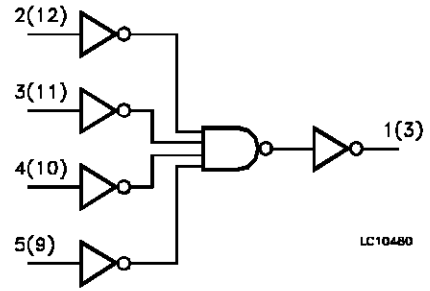
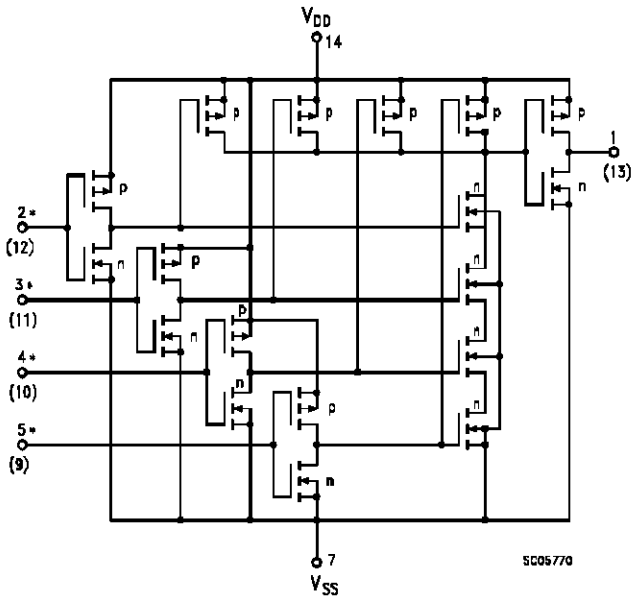
1 OF 4 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR OTHER GATE)



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SCHEMATIC AND LOGIC DIAGRAMS (continued)

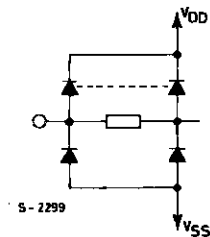
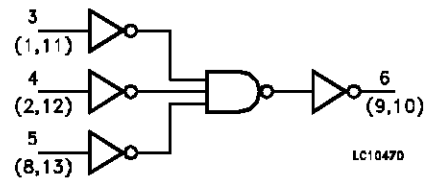
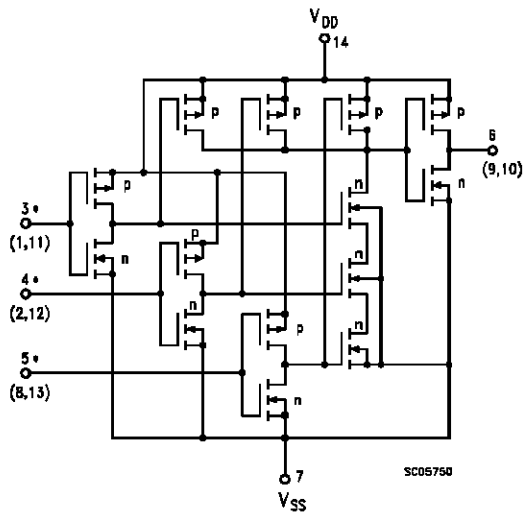
4002B



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1 OF 2 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR SECONDD GATE)

4025B



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

INVERTER AND 1 OF 3 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR OTHER GATES)

**STATIC ELECTRICAL CHARACTERISTICS** (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   ( $\mu$ A)	V <sub>DD</sub> (V)	T <sub>LOW</sub> *		25 °C			T <sub>HIGH</sub> *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I <sub>L</sub>	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	$\mu$ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
V <sub>OH</sub>	Output High Voltage		0/5		< 1	5	4.95		4.95			4.95	V	
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V <sub>OL</sub>	Output Low Voltage		5/0		< 1	5		0.05			0.05	0.05	V	
			10/0		< 1	10		0.05			0.05	0.05		
			15/0		< 1	15		0.05			0.05	0.05		
V <sub>IH</sub>	Input High Voltage			0.5/4.5	< 1	5	3.5		3.5			3.5	V	
				1/9	< 1	10	7		7			7		
				1.5/13.5	< 1	15	11		11			11		
V <sub>IL</sub>	Input Low Voltage			4.5/0.5	< 1	5		1.5			1.5	1.5	V	
				9/1	< 1	10		3			3	3		
				13.5/1.5	< 1	15		4			4	4		
I <sub>OH</sub>	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I <sub>OL</sub>	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	HCC Types	0/18	Any Input		18		$\pm$ 0.1		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.1		$\pm$ 1	$\mu$ A
		HCF Types	0/15											
C <sub>I</sub>	Input Capacitance			Any Input					5	7.5			pF	

\* T<sub>LOW</sub> = -55 °C for HCC device; -40 °C for HCF device.

\* T<sub>HIGH</sub> = +125 °C for HCC device; +85 °C for HCF device.

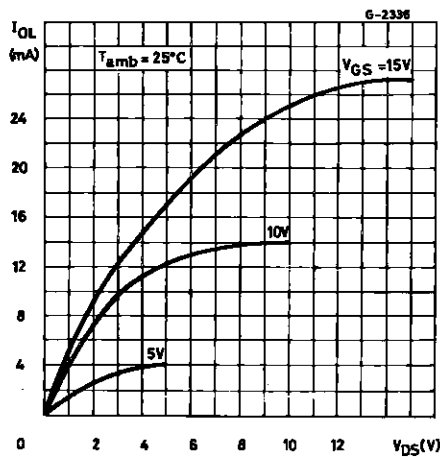
The Noise Margin for both "1" and "0" level is: 1V min. with V<sub>DD</sub> = 5V, 2V min. with V<sub>DD</sub> = 10V, 2.5V min. with V<sub>DD</sub> = 15V

# HCC/HCF4000B-4001B-4002B-4025B

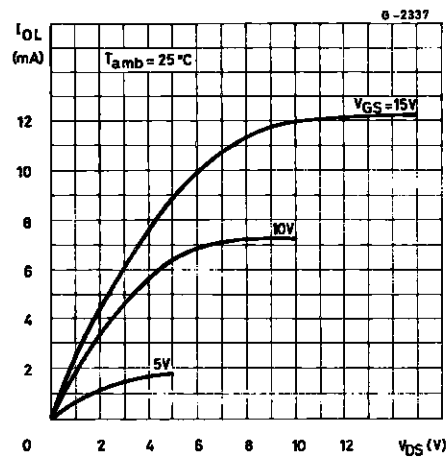
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ ,  $C_L = 50\text{ pF}$ ,  $R_L = 200\text{ K}\Omega$ , typical temperature coefficient for all  $V_{DD}$  values is  $03\text{ } \%/^{\circ}\text{C}$ , all input rise and fall times =  $20\text{ ns}$ )

Symbol	Parameter	Test Conditions		Value			Unit
			$V_{DD}$ (V)	Min.	Typ.	Max.	
$t_{PHL}$ $t_{PLH}$	Propagation Delay Time		5		125	250	ns
			10		60	120	
			5		45	90	
$t_{THL}$ $t_{TLH}$	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

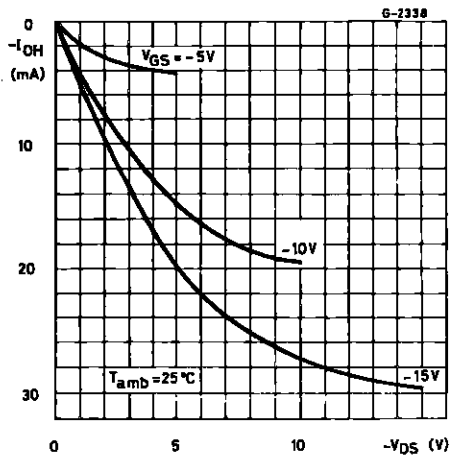
Typical Output Low (sink) Current Characteristics



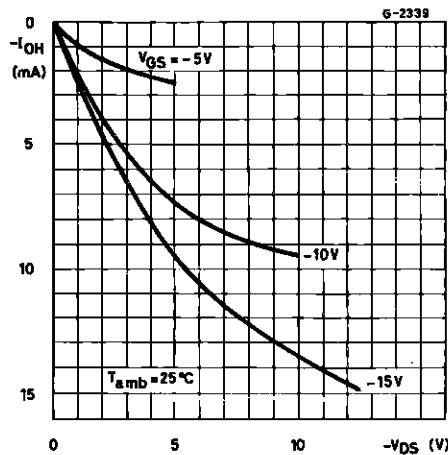
Minimum Output Low (sink) Current Characteristics



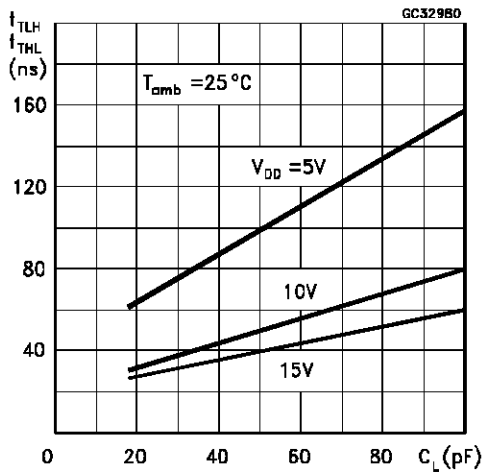
Typical Output High (source) Current Characteristics



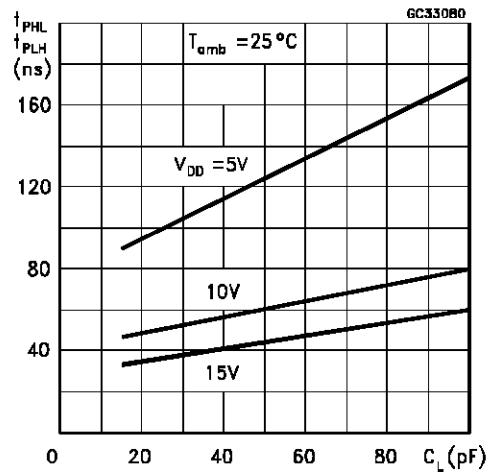
Minimum Output High (source) Current Characteristics



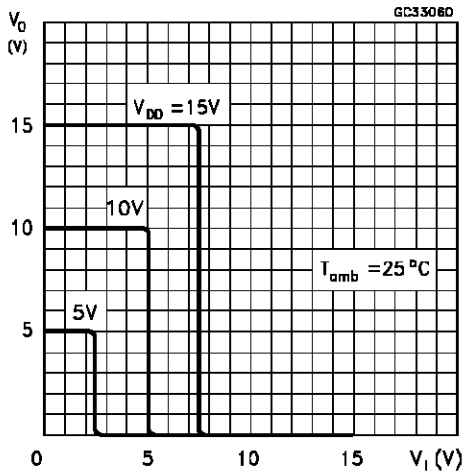
Typical Transition Time vs Load Capacitance



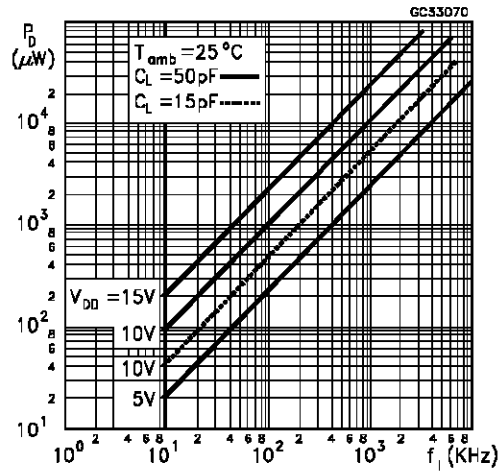
Typical Propagation Delay Time vs Load Capacitance



Typical Voltage Transfer Characteristics as a Function of Temperature

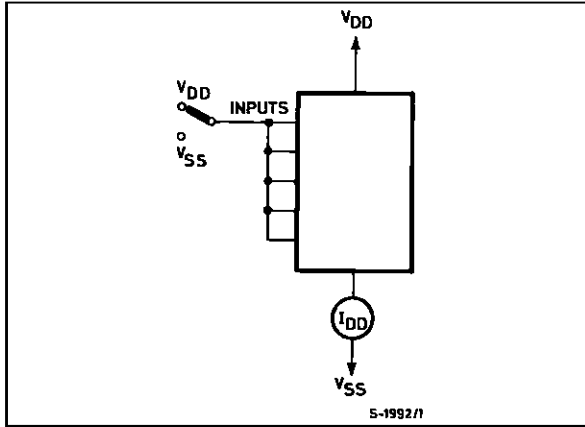


Typical Power Dissipation Per Gate vs Frequency

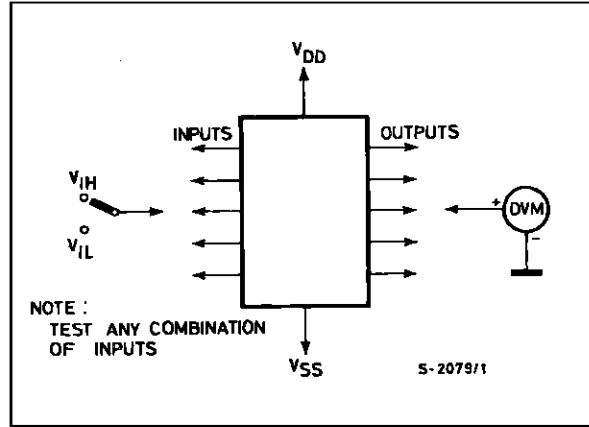


TEST CIRCUITS

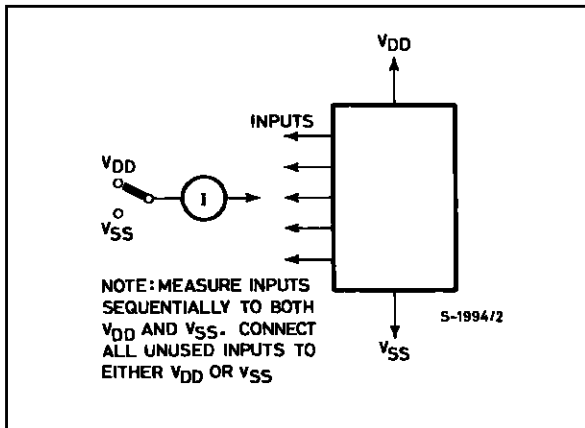
Quiescent Device Current



Noise Immunity.



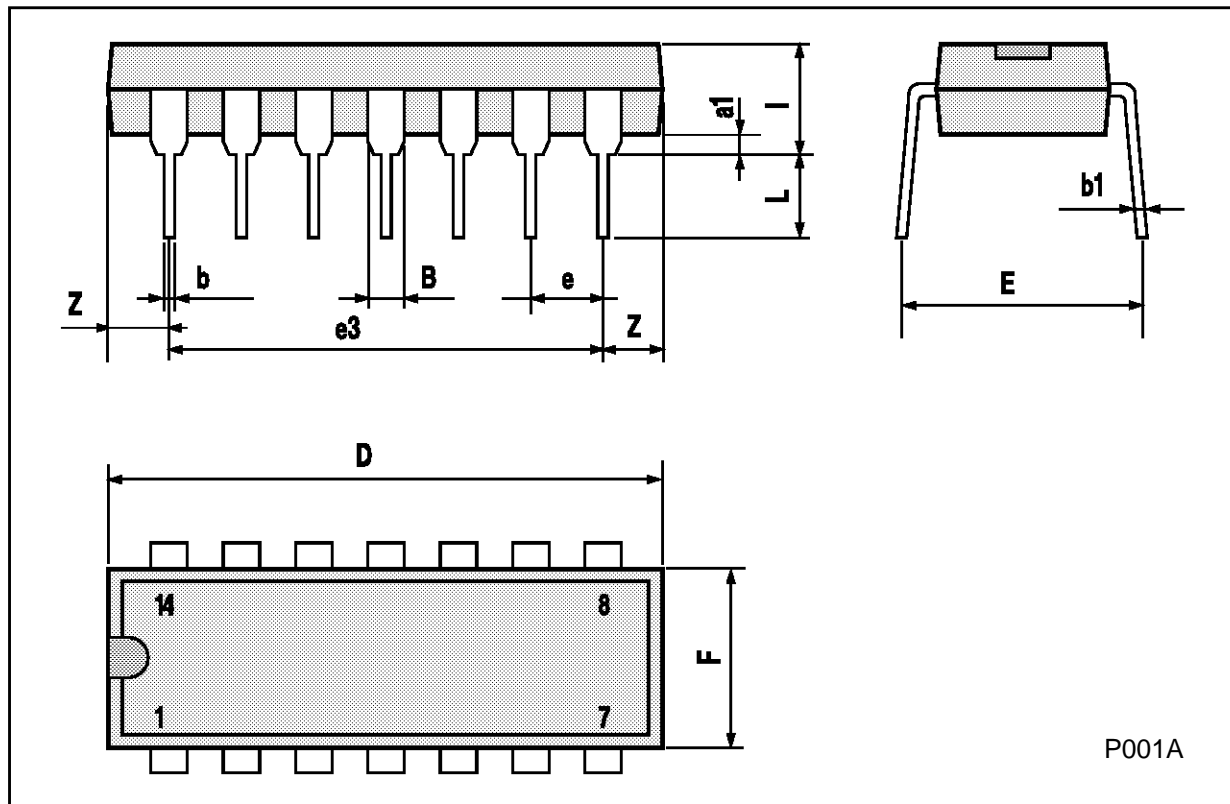
Input Leakage Current.





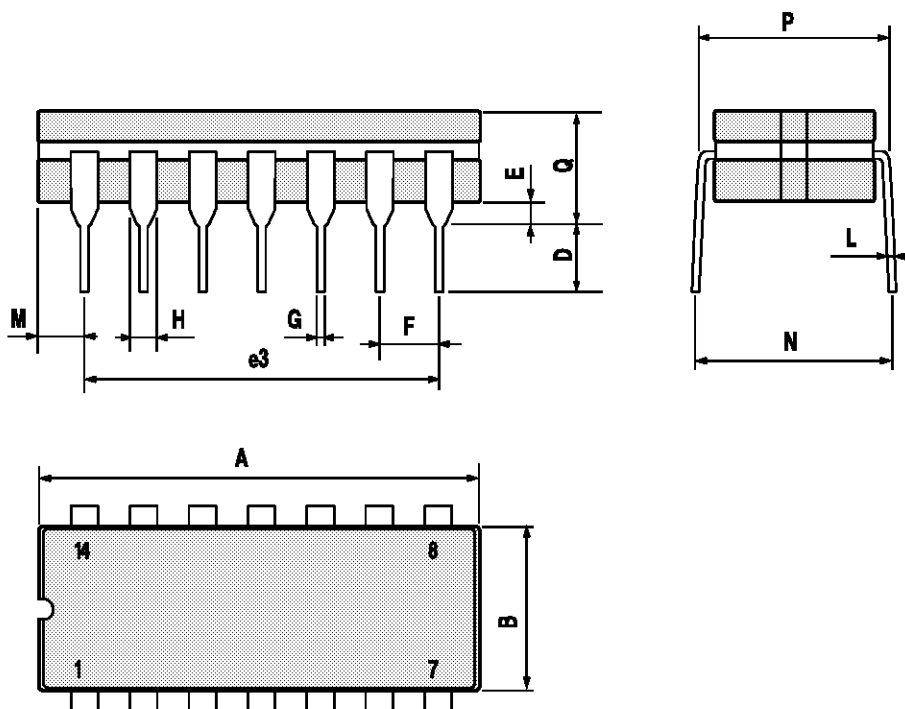
**Plastic DIP14 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



Ceramic DIP14/1 MECHANICAL DATA

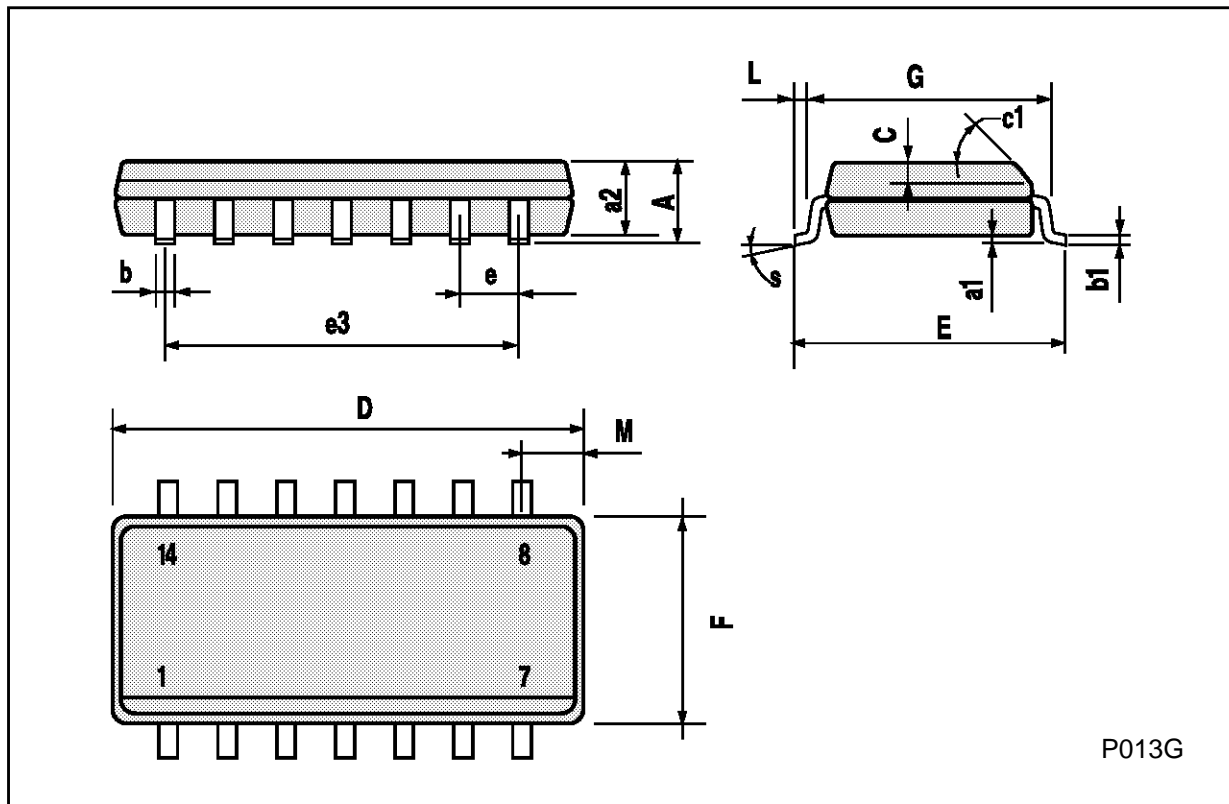
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

**SO14 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

**PLCC20 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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